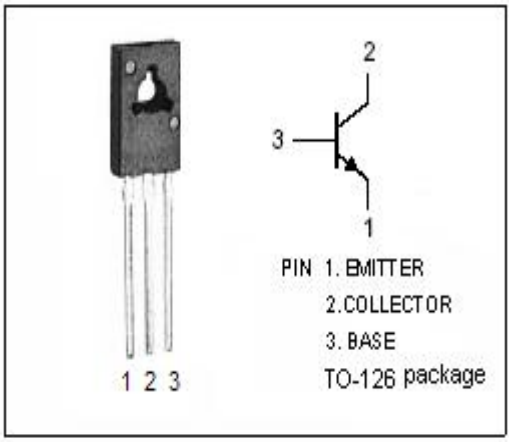
isc Silicon NPN Power Transistor — BD226/228/230

DESCRIPTION

- DC Current Gain-
  : h_{FE}= 40(Min)@ I_C= 0.15A
- Complement to Type BD227/229/231
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

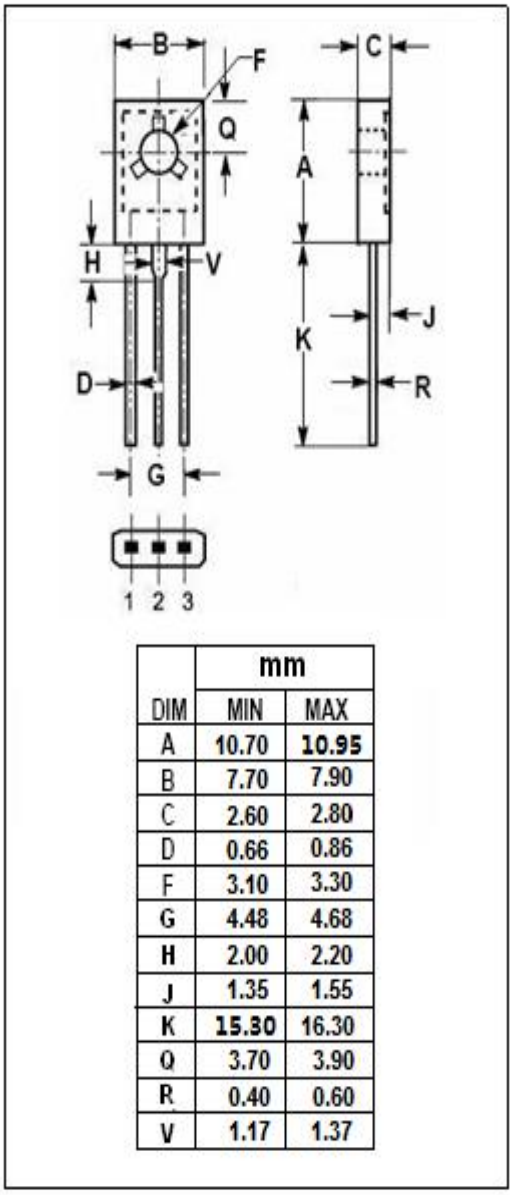


APPLICATIONS

- Designed for use in driver stages in television circuits.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER		VALUE	UNIT
V_{CBO}	Collector-Base Voltage	BD226	45	V
		BD228	60	
		BD230	100	
V_{CEO}	Collector-Emitter Voltage	BD226	45	V
		BD228	60	
		BD230	80	
V_{CER}	Collector-Emitter Voltage(R_{BE}= 1kΩ)	BD226	45	V
		BD228	60	
		BD230	100	
V_{EBO}	Emitter-Base Voltage		5	V
I_C	Collector Current-Continuous		1.5	A
I_{CM}	Collector Current-Peak		3.0	A
P_C	Collector Power Dissipation @ T_C≤62℃		12.5	W
T_J	Junction Temperature		150	℃
T_{stg}	Storage Temperature Range		-65~150	℃



DIM	mm MIN	MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	7	℃/W
$R_{th\ j\text{-}a}$	Thermal Resistance,Junction to Ambient	100	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	BD226	I_C= 50mA ; I_B= 0	45			V
		BD228		60			
		BD230		80			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage		I_C= 1A; I_B= 0.1A			0.8	V
$V_{BE(on)}$	Base-Emitter On Voltage		I_C= 1A; V_{CE}= 2V			1.3	V
I_{CBO}	Collector Cutoff Current		V_{CB}= 30V; I_E= 0 V_{CB}= 30V; I_E= 0,T_C=125℃			0.1 10	μA
I_{EBO}	Emitter Cutoff Current		V_{EB}= 5V; I_C=0			10	μA
h_{FE-1}	DC Current Gain		I_C= 5mA ; V_{CE}= 2V	25			
h_{FE-2}	DC Current Gain		I_C= 1A ; V_{CE}= 2V	25			
h_{FE-3}	DC Current Gain		I_C= 0.15A ; V_{CE}= 2V	40		250	
f_T	Current-Gain—Bandwidth Product		I_C= 50mA ; V_{CE}= 5V		125		MHz